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<b>(21) International Application Number:</b> PCT/US98/25144  <b>(22) International Filing Date:</b> 24 November 1998 (24.11.98)  <b>(30) Priority Data:</b> 08/980,386      28 November 1997 (28.11.97)      US  <b>(71) Applicant:</b> LASER TECHNOLOGY WEST, LIMITED [US/US]; 1605 South Murray Boulevard, Colorado Springs, CO 80916 (US).  <b>(72) Inventors:</b> HODSDEN, John, B.; 825 Pollux Drive, Colorado Springs, CO 80906 (US). HODSDEN, Jeffrey, Burgess; 825 Pollux Drive, Colorado Springs, CO 80906 (US).  <b>(74) Agents:</b> WAHL, John, R. et al.; Holland & Hart L.L.P., Suite 3200, 555 17th Street, P.O. Box 8749, Denver, CO 80201-8749 (US).		<b>(81) Designated States:</b> CA, CN, JP, KR, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).  <b>Published</b> <i>Without international search report and to be republished              upon receipt of that report.</i>
<b>(54) Title:</b> CONTINUOUS WIRE SAW LOOP AND METHOD FOR MANUFACTURE THEREOF		
<b>(57) Abstract</b>  <p>A closed loop wire saw loop, a method for making the closed wire saw loop, and an apparatus and method for slicing a work piece, in particular, a polysilicon or single crystal silicon ingot, utilizing a closed loop of diamond impregnated wire in which the work piece (or ingot) is rotated about its longitudinal axis as the diamond wire is driven orthogonally to it and advanced from a position adjoining the outer diameter ("OD") of the ingot towards its inner diameter ("ID"). In this manner, the diamond wire cuts through the work piece at a substantially tangential point to the circumference of the cut instead of through up to the entire diameter of the piece and single crystal silicon ingots of 300mm to 400mm or more may be sliced into wafers relatively quickly, with minimal "kerf" loss and less extensive follow-on lapping operations. The closed wire saw loop is made by squaring and welding the wire ends together and then twice heat treating the weld at about 1500 F.</p>		

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## CONTINUOUS WIRE SAW LOOP AND METHOD FOR MANUFACTURE THEREOF

### BACKGROUND OF THE INVENTION

#### **Field of the Invention:**

The present invention relates, in general, to the field of an apparatus and method for accurately sawing a work piece into two or more sections. More particularly, the present invention relates to an endless wire saw and a method for making an endless wire saw for cropping and/or slicing crystalline ingots, such as relatively large diameter polysilicon and single crystal silicon ingots.

#### **Description of the Related Art:**

The vast majority of current semiconductor and integrated circuit devices are fabricated on a silicon substrate. The substrate itself is initially created utilizing raw polycrystalline silicon having randomly oriented crystallites. However, in this state, the silicon does not exhibit the requisite electrical characteristics necessary for semiconductor device fabrication. By heating high purity polycrystalline silicon at temperatures of about 1400 degrees, a single crystal silicon seed may then be added to the melt and a single crystalline ingot pulled having the same orientation of the seed. Initially, such silicon ingots had relatively small diameters of on the order of from one to four inches, although current technology can produce ingots of 150mm (six inches) or 200mm (eight inches) in diameter. Recent improvements to crystal growing technology now allow ingots of 300mm (twelve inches) or 400mm (sixteen inches) in diameter to be produced.

Once the ingot has been produced, it must be cropped (i.e. the "head" and "tail" portions of the ingot must be removed) and then sliced into individual wafers for subsequent processing into a number of die for discrete or integrated circuit semiconductor devices. One method for cropping the ingot is through the use of a band saw having a relatively thin flexible blade. However, the large amount of flutter inherent in the band saw blade results in

a very large "kerf" loss and cutting blade serration marks which must then be lapped off.

One technique of slicing a semiconductor ingot into wafers is the slurry saw. The slurry saw comprises a series of mandrels about which a very long wire is looped and then driven through the ingot as a silicon carbide or boron carbide slurry is dripped onto the wire. Wire breakage is a significant problem and the saw down time can be significant when the wire must be replaced. Further, as ingot diameters increase to 300mm to 400mm the drag of the wire through the ingot reaches the point where breakage is increasingly more likely unless the wire gauge is increased resulting in greater "kerf" loss. Importantly, a slurry saw can take many hours to cut through a large diameter ingot.

A much preferred technique for slicing an ingot into wafers is disclosed in copending patent application Serial No. 08/888,952, filed July 7, 1997 and entitled Apparatus and Method For Slicing A Workpiece Utilizing A Diamond Impregnated Wire, the disclosure of which is hereby incorporated by reference in its entirety. This technique is a method for slicing a work piece, in particular, a polysilicon or single crystal silicon ingot utilizing a length of diamond impregnated wire in which the work piece (or ingot) is rotated about its longitudinal axis as the diamond wire is driven back and forth orthogonally to the longitudinal axis of the work piece and advanced from a position adjoining the outer diameter ("OD") of the ingot towards its inner diameter ("ID"). In this manner, the diamond wire cuts through the work piece at a point substantially tangential to the circumference of the cut instead of through up to the entire diameter of the piece. Through use of this technique, polysilicon or single crystal silicon ingots of 300mm to 400mm or more may be sliced into wafers relatively quickly, with minimal "kerf" loss and less extensive follow-on lapping operations.

There is no known continuous wire saw loop that can be used to make these extremely fine cuts. Consequently, the apparatus for sectioning a substantially cylindrical crystalline work piece with this technique uses a

relatively long length of wire having a plurality of cutting elements affixed thereto which has both ends wrapped around a capstan which alternately rotates first in one direction and then an opposite direction, while the work piece rotates continuously in one direction or alternately in opposite directions to the movement of the wire. This technique and apparatus results in faster, finer cuts than the slurry saw can produce.

Laser Technology West, Limited, Colorado Springs, Colorado, a manufacturer and distributor of diamond impregnated cutting wires and wire saws, has previously developed and manufactured a proprietary diamond impregnated wire marketed under the trademarks Superwire<sup>TM</sup> and Superlok<sup>TM</sup>. These wires comprise a very high tensile strength steel core with an electrolytically deposited surrounding copper sheath into which very small diamonds (on the order of between 20 to 120 microns) are uniformly embedded. A nickel overstrike in the Superlok wire serves to further retain the cutting diamonds in the copper sheath.

The band saw technique discussed first above requires an endless loop saw blade band. Such an endless loop would be extremely efficient at cutting ingots. In addition, multi-loop band saws machines could be constructed to make simultaneous cuts and thus greatly shorten the processing time for these ingots. However, in order to accurately cut without significant kerf losses and scoring of the cut surfaces, an extremely fine wire saw loop would be required instead of a band, using a wire such as the diamond impregnated wire described in the previous paragraph.

Unfortunately, known attempts to make a suitable wire saw loop that can withstand the stresses of operation have all failed. These wire saw wires are extremely small diameter wires, on the order of .005-.015 inch diameter wire. The formation of a wire loop requires welding the ends of the wire together. The welding of such wire materials together forms a brittle region at the weld, thus predisposing the wire loop to failure at the weld location. Conventional teachings require that the ends of the wire must be either shaped to have a slanted end surface so that the ends overlap in order

to have a sufficient surface area at the weld location or shaped to provide blunted and rounded tips that are abutted and then melted together during the weld process. The overlapping and blunting results in a thickened, embrittled region at the weld which can bind in the saw kerf, leading to immediate wire breakage. Conventional annealing and heat treating of the weld leads to weakened wire strengths at the weld, again leading to premature failures. Thus an appropriate closed wire saw loop that can be used is lacking in the prior art. Attempts to fabricate a suitable wire loop in the past have all resulted in unacceptable breakage at the weld location. Consequently, closed wire saw loops are simply unknown in the semiconductor wafer manufacturing industry.

Therefore there is a need for diamond impregnated closed wire saw loop for use in cutting a work piece such as a semiconductor crystal ingot into thin, accurately cut wafers, an apparatus for such a saw loop, and a method of making such a wire saw loop that overcomes the above problems.

### **SUMMARY OF THE INVENTION**

A method of forming a continuous or closed loop of wire having a plurality of cutting elements affixed thereto in accordance with the present invention comprises the steps of:

- 1) providing a steel wire having a tensile strength of at least 300,000 psi and having opposite ends;
- 2) butting the wire ends together;
- 3) welding the wire ends together creating a weld;
- 4) heating the welded wire ends and the weld to a temperature between 1450 F and 1550F and allowing the welded ends and the weld to air cool;
- 5) removing excess weld material from the weld and the welded ends;
- 6) again heating the welded wire ends and the weld to a temperature between 1450 F and 1550 F and allowing the welded ends and the weld to air cool.

More preferably, the method according to the invention comprises the steps of:

- 1) providing a steel wire having a central wire axis and a tensile strength of at least 300,000 psi;
- 2) squaring each of the ends of the wire to form surfaces at right angles to the axis of the wire;
- 3) butting the end surfaces of the wire ends coaxially together;
- 4) applying an electrical current through the ends to electrically weld the ends of the wire together;
- 5) heating the welded together ends to about 1500 degrees Fahrenheit;
- 6) allowing the welded ends to air cool to less than about 500 degrees Fahrenheit;
- 7) removing excess weld material from the welded ends until the weld diameter substantially equals the wire diameter;
- 8) again heating the welded together ends to about 1500 degrees Fahrenheit followed by air cooling; and
- 9) affixing an abrasive material to the surface of the wire loop.

A wire endless loop in accordance with the present invention has a wire diameter of less than .020 inch and preferably between about .008 inch and .012 inch and is formed of a steel wire having a high tensile strength of at least 300,000 psi and a highly stable carbon matrix. One such steel is commonly known as "Carpenters Stainless Steel Type 321". The wire loop abrasives are preferably fastened and distributed uniformly over the outer surface of the wire loop.

An apparatus for sectioning a semiconductor work piece in accordance with the invention preferably includes at least one continuous closed wire saw loop, a wire drive mechanism for moving the wire orthogonally with respect to the work piece longitudinal axis, a work piece rotation mechanism for rotating the workpiece about its axis, a wire advancing mechanism for positioning the wire from a first position proximate an outer diameter of the work piece to a second position proximate the axis of the work piece or inner

diameter thereof. The wire saw loop continuously moves tangentially to the cut as the saw wire loop simultaneously advances through the work piece to its center or inner diameter, at which point the cut is complete. The apparatus may include a number of wire saw loops on the drive mechanism for making a like number of cuts simultaneously. The apparatus may also be configured as above but without a work piece rotation mechanism for those applications where tangential cutting of a work piece is not required.

Still further disclosed herein is a semiconductor wafer made by a process which comprises the steps of providing a continuous loop of wire having a plurality of cutting elements affixed thereto, continuously moving the wire loop orthogonally to a longitudinal axis of a crystalline semiconductor material ingot, rotating the ingot about its longitudinal axis and advancing the wire loop from a first position proximate an outer diameter of the ingot to a second position proximate an inner diameter thereof.

Other objects, features and advantages of the present invention will become apparent from a reading of the following detailed description when taken in conjunction with the accompanying drawing wherein a particular embodiment of the invention is disclosed as an illustrative example.

### **BRIEF DESCRIPTION OF THE DRAWINGS**

Fig. 1 is a simplified representational view of an apparatus for slicing a work piece, in particular a single crystal silicon ingot, in accordance with an exemplary implementation of the present invention;

Fig. 2 is a perspective view of a complete wire saw loop in accordance with the present invention;

Fig. 3 is an enlarged cross sectional view of the wire loop taken along the line 3-3 in Fig. 2.

Fig. 4a through 4e are sequential views of the weld formation method for the wire loop shown in Figs. 2 and 3. Specifically,

Fig. 4a is a schematic side view of a pair of loop ends prior to squaring the ends.



Fig. 4b is a side view of the pair of loop ends of wire abutted together and placed in resistance welder clamps.

Fig. 4c is a side view as in 4b after the ends are welded together.

Fig. 4d is a side view of the weld region after heat treatment in an annealing chamber.

Fig. 4e is a side view of the weld region after removal of excess weld material and following a second heat treatment in an annealing chamber.

### DETAILED DESCRIPTION OF THE INVENTION

With reference now to Fig. 1, a simplified representational view of an apparatus **10** for slicing a generally cylindrical work piece, for example, a polysilicon or single crystal silicon, gallium arsenide (GaAs) or other crystalline ingot **14**, is shown. The apparatus **10** comprises, in pertinent part, one or more cutting wire loops **12** made in accordance with the invention. Each of the wire saw loops **12** is utilized to accurately and rapidly crop and saw a generally cylindrical silicon ingot **14** into multiple silicon wafers for subsequent processing into discrete or integrated circuit devices.

The apparatus **10** includes a wire drive mechanism **16** for moving one or a plurality of wire saw loops **12** in a single direction as indicated by the arrow with respect to the longitudinal axis of the ingot **14**. The wire drive mechanism **16**, in the embodiment shown, drives a driven friction wheel **18** to move the wire around two guide pulleys **20** while tension is maintained by a tension pulley **22**.

The apparatus **10** optionally further includes a work piece rotation mechanism **24**, as shown, for rotating the ingot **14** about its longitudinal axis as the wire loop **12** is moved orthogonally with respect to the ingot **14**. The work piece rotation mechanism **24**, in the embodiment shown, may comprise one or more rotating collet fixtures **26** circumferentially surrounding the ingot **14** at positions along its length thereof. The collet fixtures **26**, and hence the ingot **14**, may be rotated by means of a number of

drive rollers **28** or functionally equivalent elements. In an alternative embodiment, the ingot **14** may be secured to an end mounted work piece rotation mechanism **24** in lieu of the embodiment illustrated in this figure.

The apparatus **10** also includes a wire advancing mechanism **30** to which, in the embodiment illustrated, the wire drive mechanism **16** is mounted. The wire advancing mechanism **30** functions to advance the moving wire loop **12** from an initial position **32** displaced outwardly from, and proximate to, the outer diameter ("OD") of the ingot **14** towards a final position **34** proximate the inner diameter ("ID") of the ingot **14** to effectuate completion of a single cut. At this point, the motion of the wire advancing mechanism **30** may be reversed to withdraw the wire **12** back towards the initial position **32**.

Alternatively, the wire advancing mechanism **30** may be configured to advance the moving wire loop **12** completely through the ingot **14** if the ingot rotating mechanism is not used. Also, in applications wherein repeated cuts or slices through the ingot **14** are desired, the apparatus **10** may further incorporate a work piece repositioning mechanism **36** to enable an indexed, translational repositioning of the ingot **14** to enable the wire **12** to make repeated cuts along its length, for example, to slice a number of wafers therefrom. In the embodiment of the apparatus shown in Fig. 1, the work piece repositioning mechanism **36** may include a programmably index driven lead screw **38** which reposition the work piece rotation mechanism **24** and ingot **14** as supported by a number of rollers **40** with respect to the wire saw **12**. In alternative embodiments, the wire drive mechanism **16** and wire advancing mechanism **30** may be repositionable with respect to a generally fixed position work piece rotation mechanism **24**.

The wire saw loop **12** is shown separately in Fig. 2 and in a sectional view in Fig. 3. With particular reference to Fig. 2, the wire saw loop **12** is made of a wire core **40** which has two ends **42** and **44** joined together by a weld **46**. The wire core **40** of the loop **12** is made from carpenter stainless

steel type 321. Carpenter Stainless Steel Type 321 is an austenitic chrome nickel steel. Metallurgical literature states that this steel should be annealed at 1750-1950 F followed by water quench. According to the literature, stabilizing should be done at 1550 to 1650 F. Surprisingly, it has been found that this particular type of stainless steel, when fabricated into wire core **40** having a diameter of less than about .016 inches and a tensile strength of between 300,000 to 400,000 psi, and more preferably between 350,000 and 400,000 psi can be resistively welded together and conditioned at a temperature in a range between about 1450 F to about 1550 F and preferably at about 1500 F to substantially return its characteristic properties at the weld location to a before weld condition. Thus the wire **40** at the weld **46** becomes as flexible and as strong as the remainder of the wire loop **12** when conditioned in accordance with the present invention.

It has also been experimentally determined that the wire end surfaces should be squared rather than slanted and abutted together at about right angles to the axis of the wire during the welding operation. Also, the heat treatment at elevated temperature must be performed twice, once before weld material removal and once after weld material removal.

The method of forming the wire loop **12** in accordance with the present invention basically comprises the following steps;

- 1) providing a steel wire having a tensile strength of at least 300,000 psi and having opposite ends **42** and **44** as shown in Fig. **4a**;
- 2) butting the wire ends together as is shown in Fig. **4b**;
- 3) welding the wire ends together creating a weld as shown in Fig. **4c**;
- 4) heating the welded wire ends and the weld as shown in Fig. **4d** to a temperature between 1450 F and 1550F and allowing the welded ends and the weld to air cool;
- 5) removing excess weld material from the weld and the welded ends as shown in Fig. **4e**;
- 6) again heating the welded wire ends and the weld to a temperature

between 1450 F and 1550 F and allowing the welded ends and the weld to air cool.

More preferably, the method of forming the closed wire loop **12** comprises the steps of:

- 1) providing a piece of high strength stainless steel wire **40** having opposite ends **42** and **44** as shown in Fig. **4a**;
- 2) squaring off each of the ends **42**, **44** to form an end surface orthogonal to the axis through the wire **40**;
- 3) placing the ends **42** and **44** of the wire **40** together abutting each other coaxially in a resistance welder **50**;
- 4) applying an electrical current through the welder **50** effective to weld the abutting wire ends **42** and **44** together at temperatures in a range of 2100-3000 F forming a weld **46**;
- 5) placing the weld **46** and the welded ends **42** and **46** in a commercially available annealing chamber **52** such as a Microweld annealing chamber;
- 6) raising temperature in the annealing chamber and said welded ends to a temperature below the annealing temperature for Type 321 steel, between 1475 F and 1525 F, and preferably about 1500 F to heat treat the weld;
- 7) turn off the annealing chamber temperature control and allowing the chamber **52** and the weld **46** to cool to at least less than 500 F and preferably to ambient temperature;
- 8) removing the welded ends **42** and **44** from the chamber **52** and removing excess weld material until the weld is substantially flush with, i.e. has the same diameter as the wire **40**;
- 9) placing the welded ends **42** and **44** back in the annealing chamber **52**;
- 10) raising temperature in the annealing chamber a second time to bring said welded ends **42**, **44** and said weld **46** to a temperature below the

annealing temperature for Type 321 steel, between 1475 F and 1525 F, and preferably about 1500 F to heat treat the weld a second time; and

11) allowing the chamber **52** and the weld **46** to cool naturally to at least 500 F and preferably to ambient; and

12) removing the welded ends **42**, **44** from the chamber **52**.

A closed loop of wire **40** formed by the above method is essentially as strong as the unwelded length of wire **40**. The tensile strength of the unwelded wire **40** is between 300000 to 400000 psi and preferably around 375,000 to 400,000 psi. It has been experimentally found that for Carpenters' Steel Type 321, the optimum heat treatment temperature in the method of the present invention is about 1500 F. Temperatures substantially above this temperature cause premature weakening of the weld as do temperatures substantially below this temperature. There appears to be a Gaussian distribution of weld strengths close about this temperature of 1500 F with a peak strength at 1500 F.

Referring now to Figs. **4a** through **4e**, the above sequence of steps is illustrated. In Fig. **4a**, the raw ends **42** and **44** are shown prior to being squared and butted together in the welder clamps **48** as is shown in Fig. **4b**. Fig. **4c** shows the wire ends **42** and **44** welded together at weld **46**, prior to the ends being removed from the welder **50**. The welded ends **42** and **44** are next placed in an annealing oven **52** as shown in Fig. **4d**. However, the weld **46** and the ends **42** and **44** are not annealed. The temperature of the oven **52** is simply raised to about 1500 F and then turned off to allow the weld to cool to about 500 F before the weld **46** is removed.

As shown in Fig. **4e**, the excess weld material on weld **46** is ground away to leave the weld **46** flush with the surface of the wire **40**. The weld **46** is then again placed in the oven **52** and temperature raised to about 1500 F and then air cooled to below about 500 F. The closed loop of wire **40** is then removed and thoroughly allowed to cool to ambient temperature.

After formation of the wire loop as described above, the abrasive material is affixed to the wire loop. In the particular preferred embodiment

shown in Figs. 2 and 3, the wire saw loop 12 is formed with a coating of a metal 54 that is softer than the steel wire 40, such as copper or nickel. Preferably an electrolytic metal is such as copper or nickel is used. The layer of copper or nickel is electrolytically plated on the closed loop of wire 40 in an appropriate electrolytic bath and then industrial diamond particles 56 are mechanically impregnated into the layer or coating 54 to provide the abrasive substance on the wire saw loop 12. Finally, a thin layer 58 of nickel, of preferably about .0002 to .0005 inch thickness is electroplated over the entire structure to help seat the diamond abrasive particles 56.

For example, a wire diameter of about .012 inch, the copper or nickel coating 54 with diamonds 56 mechanically impregnated therein has a thickness of about .002 inch to yield an overall wire saw diameter of about .016 inch.

Other methods of adhering abrasives such as diamond particles 56 or other hard materials such as tungsten carbide to the wire 40 could also be utilized in the present invention. For example, an adhesive bonding agent may be applied to the wire and the abrasive materials bonded to the adhesive bonding agent. In this case, the glue or bonding agent would be applied to the wire surface and then the wire loop rolled through an abrasive powder.

While there have been described above the principles of the present invention in conjunction with specific apparatus and wire sawing techniques, it is to be clearly understood that the foregoing description is made only by way of example and not as a limitation to the scope of the invention. Particularly, it is recognized that the teachings of the foregoing disclosure will suggest other modifications to those persons skilled in the relevant art. Such modifications may involve other features which are already known per se and which may be used instead of or in addition to features already described herein. Although claims have been formulated in this application to particular combinations of features, it should be understood that the scope of the disclosure herein also includes any novel feature or any novel

combination of features disclosed either explicitly or implicitly or any generalization or modification thereof which would be apparent to persons skilled in the relevant art, whether or not such relates to the same invention as presently claimed in any claim and whether or not it mitigates any or all of the same technical problems as confronted by the present invention. The applicants hereby reserve the right to formulate new claims to such features and/or combinations of such features during the prosecution of the present application or of any further application derived therefrom.

**CLAIMS**

What is claimed is:

1. A method for sectioning a substantially cylindrical crystalline work piece comprising the steps of:
  - 5 providing a continuous wire loop having a plurality of cutting elements affixed thereto;  
moving said wire orthogonally to a longitudinal axis of said work piece continuously in one direction; and  
10 advancing said wire from a first position proximate an outer diameter of said work piece to a second position at least proximate said longitudinal axis.
2. The method of claim 1 wherein said step of providing is carried out by means of a diamond impregnated closed wire loop.
3. The method of claim 1 wherein said step of moving is carried  
15 out by the step of:
  - linearly drawing said wire in one direction with respect to said longitudinal axis of said work piece.
4. The method of claim 1 wherein said steps of providing and moving further comprise the steps of:
  - 20 providing a plurality of wire loops in a generally parallel and spaced apart relationship therebetween, each of said wire loops having a plurality cutting elements affixed thereto; and  
simultaneously moving said plurality of wires orthogonally to a longitudinal axis of said work piece.
- 25 5. A method of making a closed wire loop comprising the steps of:
  - a) providing a steel wire having a diameter of less than .020



inches, a tensile strength of at least 300,000 psi and having opposite ends;

b) butting the wire ends together;

c) welding the wire ends together creating a weld;

5 d) heating the welded wire ends and the weld to a temperature between 1450 F and 1550F and allowing the welded ends and the weld to air cool;

e) removing excess weld material from the weld and the welded ends; and

10 f) repeating step d).

6. The method according to claim 5 wherein step b includes shaping said ends to have an end surface orthogonal to a longitudinal axis of said wire.

7. The method according to claim 5 wherein step d is performed  
15 in a temperature range between 1475 F and 1525 F.

8. A method of forming a closed wire saw loop comprising the steps of:

a) providing a steel wire having a diameter of less than .020 inches, a central wire axis and a tensile strength of at least 300,000 psi;

20 b) squaring each of the ends of the wire to form surfaces at right angles to the axis of the wire;

c) butting the end surfaces of the wire ends coaxially together;

d) applying an electrical current through the ends to electrically weld the ends of the wire together;

25 e) heating the welded together ends to a range of 1475 to about 1525 degrees Fahrenheit;

f) allowing the welded ends to air cool to less than about 500 degrees Fahrenheit;

g) removing excess weld material from the welded ends until the

weld diameter substantially equals the wire diameter; and

h) again heating the welded together ends to within a range of 1475 to about 1525 degrees Fahrenheit followed by air cooling to a temperature less than about 500 degrees Fahrenheit.

5           9.     The method according to claim 8 further comprising the step of adhering an abrasive to an outside surface of said closed wire loop.

          10.    The method according to claim 8 wherein said temperatures in steps e and h is about 1500 F.

          11.    The method according to claim 8 wherein said tensile  
10   strength is between about 375,000 to about 400,000 psi.

          12.    An apparatus for sectioning a substantially cylindrical crystalline work piece comprising:

          at least one continuous closed wire loop having a plurality of cutting elements affixed thereto;

15           a wire drive mechanism for moving said wire orthogonally with respect to a longitudinal axis of said work piece;

          a work piece rotation mechanism coupled to said work piece for rotating said work piece about said longitudinal axis; and

          a wire advancing mechanism for positioning said wire from a first  
20   position proximate an outer diameter of said work piece to a second position proximate an inner diameter thereof.

          13.    The apparatus of claim 12 wherein said wire loop comprises a plurality of diamonds impregnated in said wire.

          14.    The apparatus of claim 13 wherein said wire loop comprises  
25   a steel core having a circumferentially surrounding copper sheath.

          15.    The apparatus of claim 14 wherein said plurality of diamonds are impregnated in said copper sheath.

16. The apparatus of claim 15 wherein said wire further comprises a nickel layer overlying said copper sheath.

17. The apparatus of claim 15 wherein said plurality of diamonds are substantially uniformly distributed about a circumference and length  
5 of said wire.

18. The apparatus of claim 12 wherein said wire drive mechanism is operative to linearly draw said wire in one direction with respect to said longitudinal axis of said work piece.

19. The apparatus of claim 18 wherein said wire comprises a  
10 closed loop of wire.

20. A wire saw loop comprising a closed loop of wire having a diameter of less than .020 inches and a tensile strength of at least 300,000 psi, a coating of electrolytic metal on said closed loop of wire, and a distributed plurality of abrasives adhered to said coating.

21. The saw loop according to claim 20 wherein said abrasives are industrial diamonds.  
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22. The saw loop according to claim 21 wherein said industrial diamonds are mechanically impregnated into said coating of electrolytic metal.

23. The saw loop according to claim 20 wherein said closed loop of wire has a diameter between about .008 inches and .016 inches.  
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24. The saw loop according to claim 23 further comprising a nickel overcoating over at least a portion of said diamonds and said nickel layer.

25. A semiconductor wafer made by a process comprising the steps of:  
25

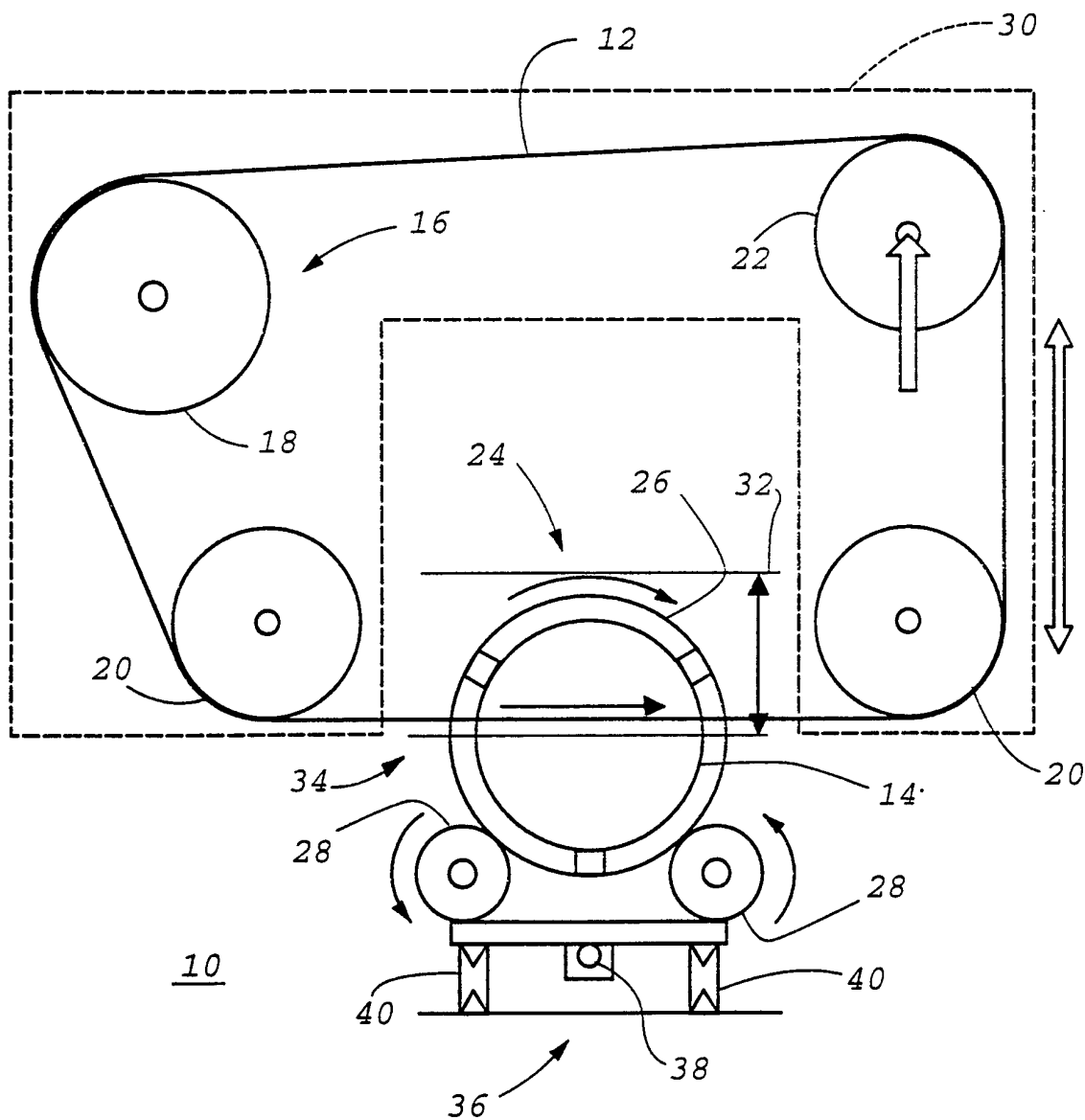
providing a closed wire saw loop having a plurality of cutting elements affixed thereto;

moving said wire continuously in one direction orthogonally to a longitudinal axis of a crystalline semiconductor material ingot;

5 rotating said ingot about said longitudinal axis; and

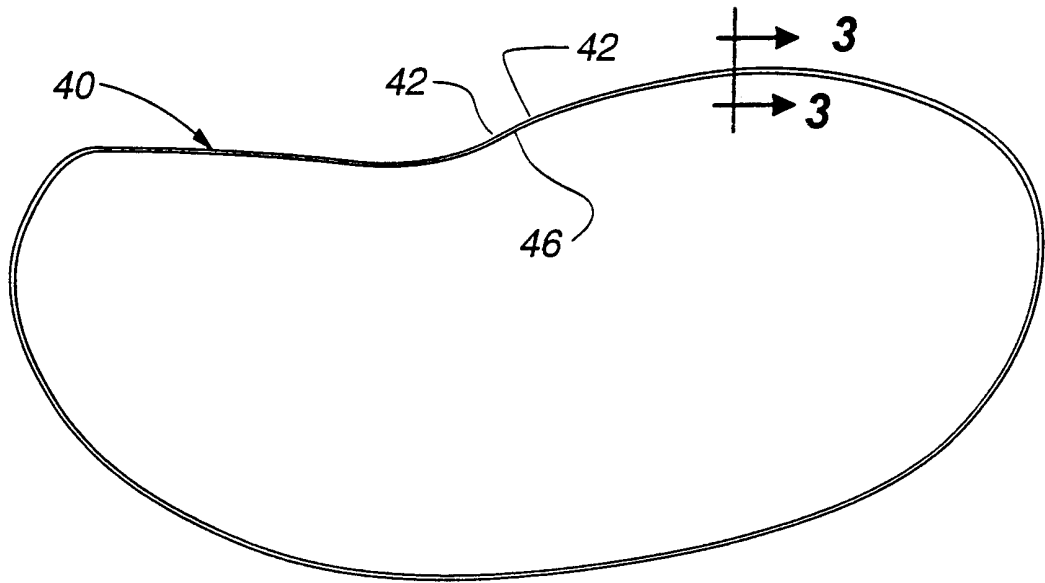
advancing said wire from a first position proximate an outer diameter of said ingot through said ingot to a second position proximate at least a center of said ingot.

26. The semiconductor wafer of claim 25 wherein said step of  
10 providing is carried out by means of a diamond impregnated wire.



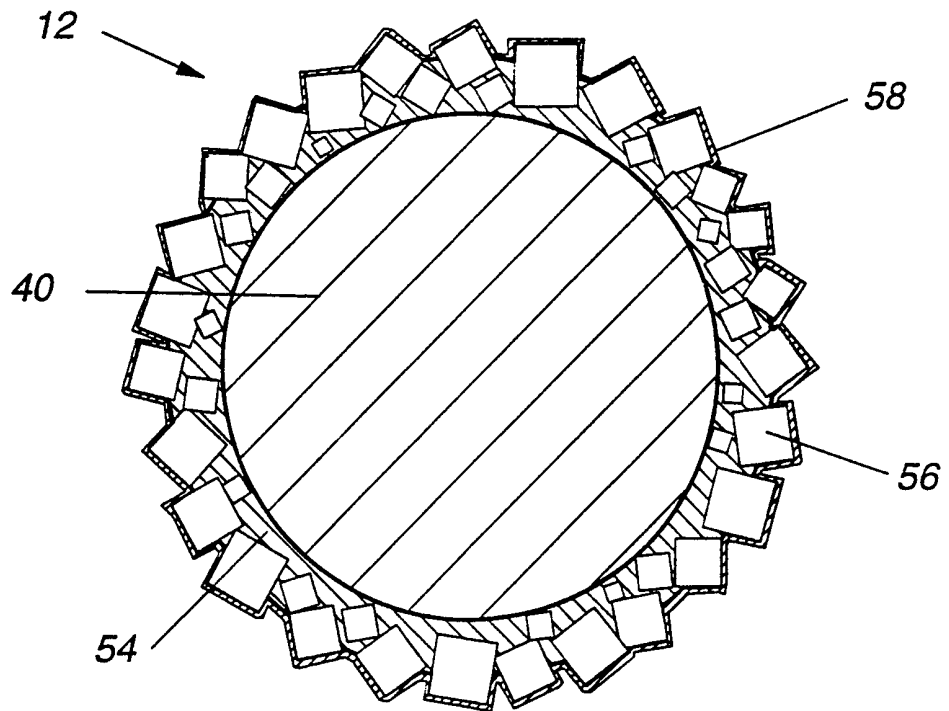
**Fig. 1**

2/3

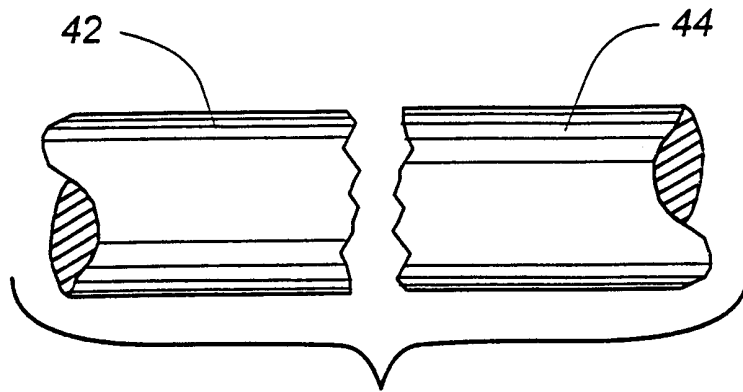


12 →

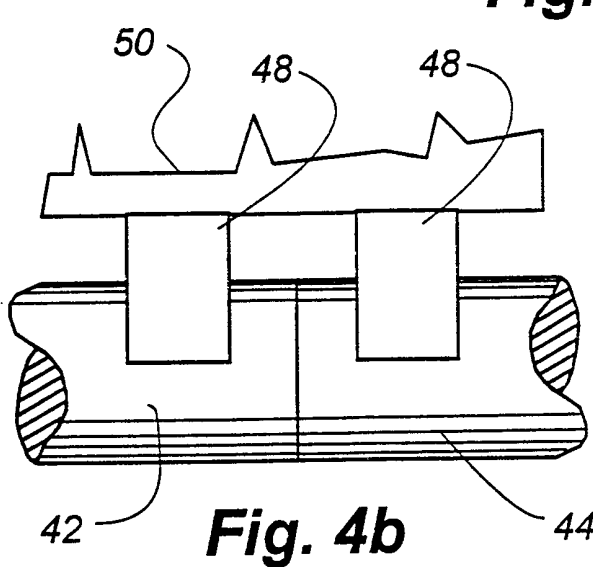
**Fig. 2**



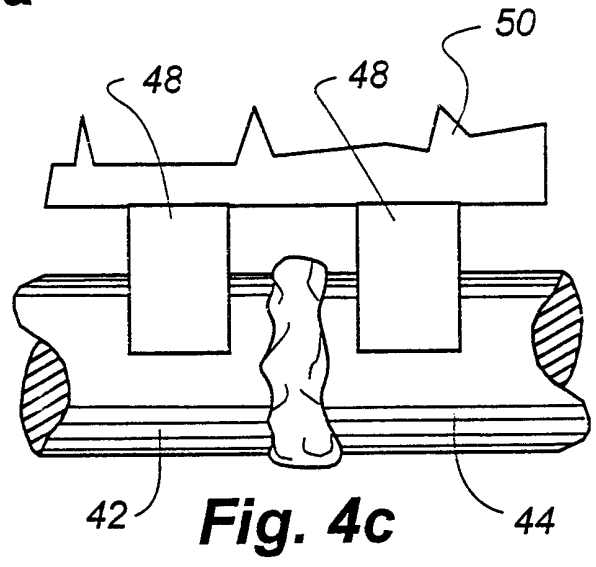
**Fig. 3**



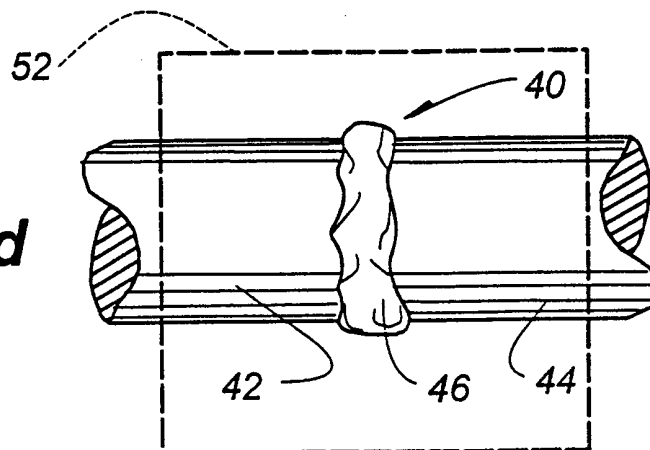
**Fig. 4a**



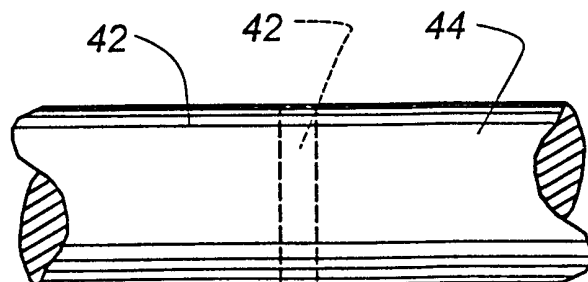
**Fig. 4b**



**Fig. 4c**



**Fig. 4d**



**Fig. 4e**